



UN2114 (3RA2114)

硅 PNP 数字三极管/SILICON PNP DIGITA TRANSISTOR

用途:用于开关、反向电路、界面电路以及驱动电路中。

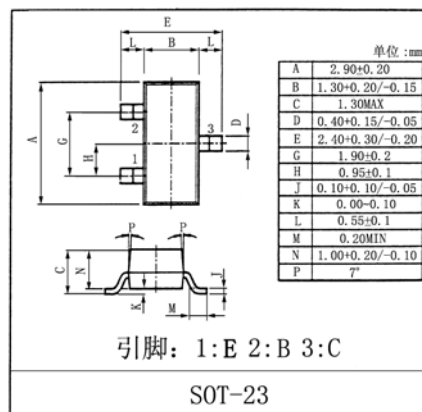
Purpose: Switching, inverter circuit, interface circuit and driver circuit applications.

特点:内装偏置电阻,简化线路设计,减少元件和制造流程。

Features: With built-in bias resistors, simplify circuit design, reduce a quantity of parts and manufacturing process.

极限参数/Absolute Maximum Ratings(Ta=25°C)

参数符号 Symbol	数值 Rating	单位 Unit
V_{CB0}	-50	V
V_{CE0}	-50	V
I_C	-100	mA
P_C	200	mW
T_j	150	°C
T_{stg}	-55~150	°C



电性能参数/Electrical Characteristics(Ta=25°C)

参数符号 Symbol	测试条件 Test Condition	数值 Rating			单位 Unit
		最小值 Min	典型值 Typ	最大值 Max	
V_{CB0}	$I_C = -10 \mu A$ $I_E = 0$	-50			V
V_{CE0}	$I_C = -2.0mA$ $I_B = 0$	-50			V
I_{CB0}	$V_{CB} = -50V$ $I_E = 0$			-0.1	μA
I_{CE0}	$V_{CE} = -50V$ $I_B = 0$			-0.5	μA
I_{EB0}	$V_{EB} = -6.0V$ $I_C = 0$			-0.2	mA
h_{FE}	$V_{CE} = -10V$ $I_C = -5.0mA$	80			
$V_{CE(sat)}$	$I_C = -10mA$ $I_B = -0.3mA$			-0.25	V
V_{OH}	$V_{CC} = -5.0V$ $V_B = -0.5V$ $R_L = 1K \Omega$	-4.9			V
V_{OL}	$V_{CC} = -5.0V$ $V_B = -2.5V$ $R_L = 1K \Omega$			-0.2	V
f_T	$V_{CB} = -10V$ $I_E = 2.0mA$ $f = 200MHz$		150		MHz
R1		7	10	13	K Ω
R2/R1		3.7	4.7	5.7	

印章/Marking: H54

等效电路图

